Low-power dual 2-input NAND gate Rev. 1 — 1 July 2019

1. General description

The 74AUP2G00-Q100 provides dual 2-input NAND function.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - MIL-STD-883, method 3015 Class 3A exceeds 5000 V
- Low static power consumption; I_{CC} = 0.9 µA (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation

3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74AUP2G00DC-Q100	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1				

nexperia

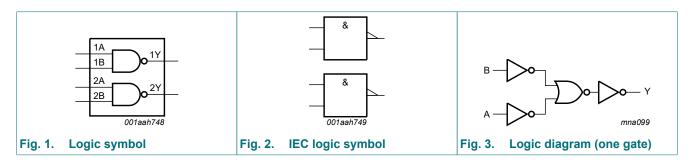
Low-power dual 2-input NAND gate

4. Marking

Table 2. Marking codes						
	Type number	Marking code[1]				
	74AUP2G00DC-Q100	p00				

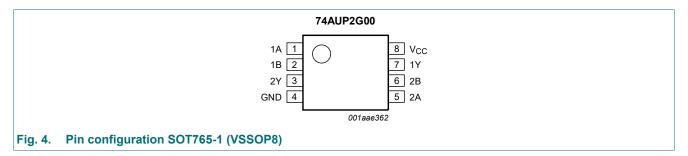
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level.

Input		Output
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
VI	input voltage	[1]	-0.5	+4.6	V
Vo	output voltage	Active mode and Power-down mode [1]	-0.5	+4.6	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$ [2]	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SOT765-1 (VSSOP8) package: above 99 °C the value of P_{tot} derates linearly with 4.9 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	-	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T _{amb} = 2	5 °C		·		·	
VIH	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{он}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I_{O} = -20 µA; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I_0 = -2.3 mA; V_{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μA
∆I _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
сс	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μA
∆I _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ [1] $V_{CC} = 3.3 \text{ V}; \text{ per pin}$	-	-	40	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V _I = GND or V _{CC}	-	0.8	-	pF
Co	output capacitance	$V_0 = GND; V_{CC} = 0 V$	-	1.7	-	pF

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -4	0 °C to +85 °C				1	
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = -20 µA; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	$0.7 \times V_{CC}$	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I_0 = -2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_0 = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
l _l	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μA
ΔI _{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
ΔI _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 V; I_{O} = 0 A;$ [1] $V_{CC} = 3.3 V;$ per pin	-	-	50	μA

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T _{amb} = -4	0 °C to +125 °C					1
VIH	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = -20 µA; V_{CC} = 0.8 V to 3.6 V	V _{CC} - 0.11	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	$0.6 \times V_{CC}$	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I_0 = -2.3 mA; V_{CC} = 2.3 V	1.77	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
l _l	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μA
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μA
∆I _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μA
lcc	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
ΔI _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 V; I_{O} = 0 A;$ [1] $V_{CC} = 3.3 V;$ per pin	-	-	75	μA

[1] One input at V_{CC} - 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 6.

Symbol	Parameter	Conditions	T	_{amb} = 25 °	°C	T _{amb}	= -40 °C t	o +125 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F								
t _{pd}	propagation	nA, nB to nY; see Fig. 5 [2]							
	delay	V _{CC} = 0.8 V	-	17.5	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.5	5.3	11.0	2.1	12.2	13.5	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	3.8	6.8	1.8	7.8	8.6	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.1	5.3	1.4	6.2	6.9	ns
		V _{CC} = 2.3 V to 2.7 V	1.3	2.5	4.0	1.1	4.7	5.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.2	3.6	1.0	4.2	4.7	ns
C _L = 10 p	ρF								
t _{pd}	propagationd	nA, nB to nY; see Fig. 5 [2]							
	elay	V _{CC} = 0.8 V	-	21.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.4	6.1	13.0	2.2	14.4	15.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.4	4.4	7.9	2.2	9.2	10.2	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	3.7	6.2	1.9	7.3	8.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	3.0	4.7	1.3	5.6	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	2.8	4.3	1.2	4.9	5.4	ns
C _L = 15 p	ρF								
t _{pd}	propagation	nA, nB to nY; see Fig. 5 [2]							
	delay	V _{CC} = 0.8 V	-	24.5	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.4	6.9	14.8	3.1	16.5	18.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.8	5.0	8.9	2.5	10.5	11.6	ns
		V _{CC} = 1.65 V to 1.95 V	2.0	4.1	7.0	2.0	8.3	9.2	ns
		V _{CC} = 2.3 V to 2.7 V	1.7	3.5	5.3	1.5	6.4	7.1	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	3.2	4.9	1.4	5.7	6.3	ns
C _L = 30 p	ρF								
t _{pd}	propagation	nA, nB to nY; see Fig. 5 [2]							
	delay	V _{CC} = 0.8 V	-	34.8	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.6	9.2	20.1	4.1	22.6	24.9	ns
		V _{CC} = 1.4 V to 1.6 V	3.0	6.5	11.8	2.9	14.0	15.4	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	5.4	9.3	2.3	11.1	12.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	4.6	7.1	2.1	8.5	9.4	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	4.3	6.5	2.1	7.6	8.4	ns

Symbol	Parameter	Conditions	T _{amb} = 25 °C		T _{amb} = -40 °C to +125 °C			Unit	
				Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pF	F, 10 pF, 15 pF	and 30 pF							
C _{PD}	power	$f_i = 1 \text{ MHz}; V_i = \text{GND to } V_{CC}$ [3]							
	dissipation capacitance	V _{CC} = 0.8 V	-	2.8	-	-	-	-	pF
	Capacitanice	V _{CC} = 1.1 V to 1.3 V	-	2.9	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	3.0	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	3.0	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	3.4	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	3.9	-	-	-	-	pF

All typical values are measured at nominal V_{CC}. [1]

 t_{pd} is the same as t_{PLH} and t_{PHL} . [2]

 C_{PD} is used to determine the dynamic power dissipation (P_D in µW). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where: [3]

f_i = input frequency in MHz;

 f_o = output frequency in MHz;

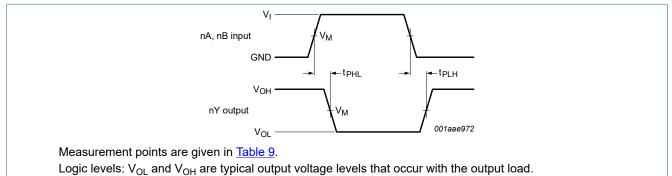
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11.1. Waveforms and test circuit



The data input (nA or nB) to output (nY) propagation delays Fig. 5.

Table 9. Measurement points

Supply voltage	Output	Input				
V _{cc}	V _M	V _M	VI	t _r = t _f		
0.8 V to 3.6 V	$0.5 \times V_{CC}$	0.5 × V _{CC}	V _{CC}	≤ 3.0 ns		

Low-power dual 2-input NAND gate

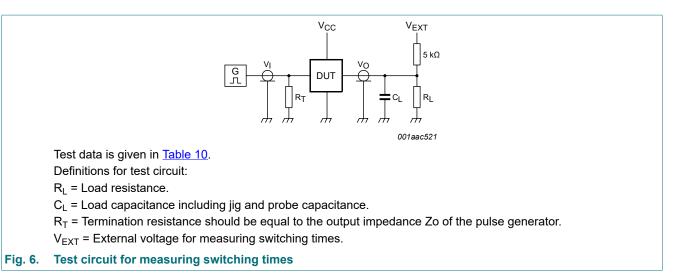


Table 10. Test data

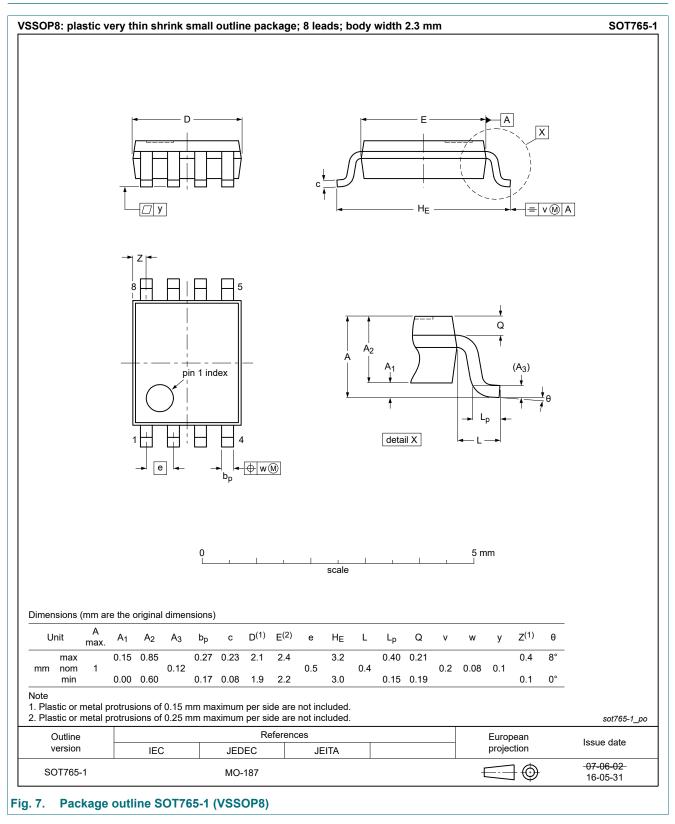
Supply voltage	Load		V _{EXT}		
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V _{CC}

[1] For measuring enable and disable times $R_L = 5 k\Omega$.

For measuring propagation delays, setup and hold times and pulse width R_L = 1 M Ω .

74AUP2G00_Q100

12. Package outline



13. Abbreviations

Table 11. Abbreviations			
Acronym	Description		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
НВМ	Human Body Model		
MM	Machine Model		
MIL	Military		

14. Revision history

Table 12. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AUP2G00_Q100 v.1	20190701	Product data sheet	-	-	

74AUP2G00_Q100

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <u>https://www.nexperia.com</u>.

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